

Title (en)
SEMI-POLAR, WURTZITE-TYPE, GROUP III NITRIDE BASED SEMICONDUCTOR LAYERS AND SEMICONDUCTOR COMPONENTS BASED THEREON

Title (de)
SEMIPOLARE WURTZITISCHE GRUPPE-III-NITRID BASIERTE HALBLEITERSCHICHTEN UND DARAUF BASIERENDE HALBLEITERBAUELEMENTE

Title (fr)
COUCHES DE SEMICONDUCTEURS À BASE DE NITRURE DU GROUPE III DE TYPE WURTZITE, SEMI-POLAIRES, ET COMPOSANTS À SEMICONDUCTEURS PRODUITS SUR LA BASE DE CES COUCHES

Publication
EP 2478551 A1 20120725 (DE)

Application
EP 10776926 A 20100916

Priority
• DE 102009042349 A 20090920
• DE 2010001094 W 20100916

Abstract (en)
[origin: WO2011032546A1] The invention relates to semi-polar, wurtzite-type, group III nitride based semiconductor layers and semiconductor components based thereon. According to the invention, group III nitride layers can be used in a plurality of ways in electronic and optoelectronic fields. The growth of said types of layers occurs, as a rule, on substrates such as sapphire, SiC and recently Si (111). The obtained layers are, as a rule, oriented in the direction of growth in a polar and/or c-axis manner. For many optoelectronic applications, and also for acoustic applications in SAWs, the growth of non or semipolar group III nitride layers is interesting and/or necessary. Said method enables the polarisation reduced group III nitride layers to grow in a simple and economical manner without prior structuring of the substrate.

IPC 8 full level
H01L 21/20 (2006.01); **H01L 21/02** (2006.01)

CPC (source: EP KR US)
H01L 21/02381 (2013.01 - EP US); **H01L 21/02433** (2013.01 - EP US); **H01L 21/02458** (2013.01 - EP US); **H01L 21/0254** (2013.01 - EP US); **H01L 21/02609** (2013.01 - EP US); **H01L 21/20** (2013.01 - KR)

Citation (search report)
See references of WO 2011032546A1

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)
WO 2011032546 A1 20110324; CN 102668027 A 20120912; DE 102009042349 A1 20110331; DE 102009042349 B4 20110616; EP 2478551 A1 20120725; JP 2013505590 A 20130214; KR 20120083399 A 20120725; TW 201126757 A 20110801; US 2012217617 A1 20120830

DOCDB simple family (application)
DE 2010001094 W 20100916; CN 201080052615 A 20100916; DE 102009042349 A 20090920; EP 10776926 A 20100916; JP 2012530124 A 20100916; KR 20127009222 A 20100916; TW 99131883 A 20100920; US 201013496957 A 20100916